

Octal 3-State Buffer, Inverting/Non-Inverting

MM74HCT540, MM74HCT541

General Description

The MM74HCT540 and MM74HCT541 3-STATE buffers utilize advanced silicon-gate CMOS technology and are general purpose high speed inverting and non-inverting buffers. They possess high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits achieve speeds comparable to low power Schottky devices, while retaining the low power consumption of CMOS. Both devices are TTL input compatible and have a fanout of 15 LS-TTL equivalent inputs.

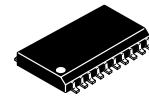
MM74HCT devices are intended to interface between TTL and NMOS components and standard CMOS devices. These parts are also plug-in replacements for LS-TTL devices and can be used to reduce power consumption in existing designs.

The MM74HCT540 is an inverting buffer and the MM74HCT541 is a non-inverting buffer. The 3-STATE control gate operates as a two-input NOR such that if either $\overline{G1}$ or $\overline{G2}$ are HIGH, all eight outputs are in the high-impedance state.

In order to enhance PC board layout, the MM74HCT540 and MM74HCT541 offers a pinout having inputs and outputs on opposite sides of the package. All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

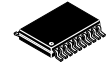
- TTL Input Compatible
- Typical Propagation Delay: 12 ns
- 3-STATE Outputs for Connection to System Buses
- Low Quiescent Current: 160 μ A
- Output Current: 6 mA (min)
- These are Pb-Free Devices



SOIC-20 WB
CASE 751D-05

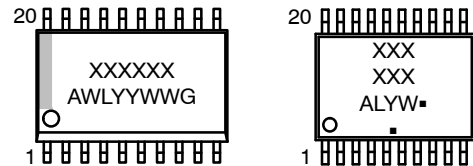


TSSOP-20 WB
CASE 948E



TSSOP-20
CASE 948AQ

MARKING DIAGRAMS

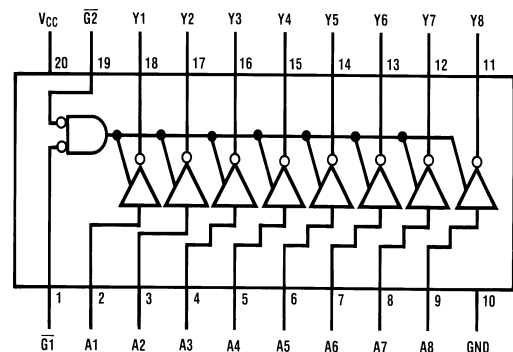


XXXXX = Specific Device Code
 A = Assembly Location
 L/WL = Wafer Lot
 YY = Year
 YW/WW = Work Week
 ■ or G = Pb-Free Package

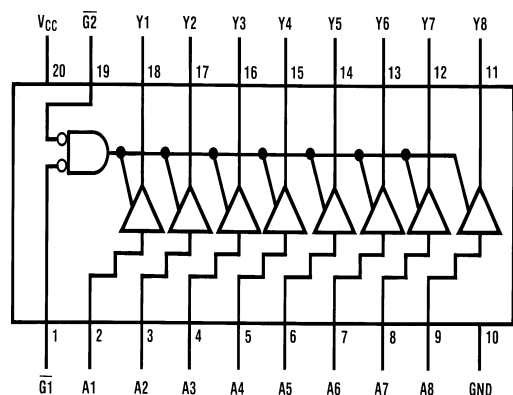
(Note: Microdot may be in either location)

CONNECTION DIAGRAMS

Pin Assignment for SOIC and TSSOP



MM74HCT540 (Top View)



MM74HCT541 (Top View)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

MM74HCT540, MM74HCT541

ABSOLUTE MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	–0.5 to +7.0	V
V _{IN}	DC Input Voltage	–0.5 to V _{CC} + 0.5	V
V _{OUT}	DC Output Voltage	–0.5 to V _{CC} + 0.5	V
I _{IK} , I _{OK}	Clamp Diode Current	±20	mA
I _{OUT}	DC Output Current, per Pin	±35	mA
I _{CC}	DC V _{CC} or GND Current, per Pin	±70	mA
T _{STG}	Storage Temperature Range	–65 to +150	°C
P _D	Power Dissipation S. O. Package Only	500	mW
T _L	Lead Temperature (Soldering 10 seconds)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Unless otherwise specified all voltages are referenced to ground.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	Supply Voltage	4.5	5.5	V
V _{IN} , V _{OUT}	DC Input or Output Voltage	0	V _{CC}	V
T _A	Operating Temperature Range	–55	+125	°C
t _r , t _f	Input Rise or Fall Times	–	500	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 5 V ±10% unless otherwise specified)

Symbol	Parameter	Conditions	T _A = 25°C		T _A = –40°C to 85°C	T _A = –55°C to 125°C	Unit
			Typ	Guaranteed Limits			
V _{IH}	Minimum HIGH Level Input Voltage		–	2.0	2.0	2.0	V
V _{IL}	Maximum LOW Level Input Voltage		–	0.8	0.8	0.8	V
V _{OH}	Minimum HIGH Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} = 20 μA I _{OUT} = 6.0 mA, V _{CC} = 4.5 V I _{OUT} = 7.2 mA, V _{CC} = 5.5 V	V _{CC} 4.2 5.2	V _{CC} –0.1 3.98 4.98	V _{CC} –0.1 3.84 4.84	V _{CC} –0.1 3.7 4.7	V
V _{OL}	Maximum LOW Level Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} = 20 μA I _{OUT} = 6.0 mA, V _{CC} = 4.5 V I _{OUT} = 7.2 mA, V _{CC} = 5.5 V	0 0.2 0.2	0.1 0.26 0.26	0.1 0.33 0.33	0.1 0.4 0.4	V
I _{IN}	Maximum Input Current	V _{IN} = V _{CC} or GND	–	±0.1	±1.0	±1.0	μA
I _{OZ}	Maximum 3–STATE Output Leakage Current	V _{OUT} = V _{CC} or GND G̅ = V _{IH}	–	±0.5	±5.0	±10	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND I _{OUT} = 0 μA	–	8.0	80	160	μA
		V _{IN} = 2.4 V or 0.5 V (Note 2)	0.6	1.0	1.3	1.5	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Measured per input. All other inputs at V_{CC} or GND.

MM74HCT540, MM74HCT541

AC ELECTRICAL CHARACTERISTICS

(MM74HCT540: $V_{CC} = 5.0\text{ V}$, $t_r = t_f = 6\text{ ns}$, $T_A = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Unit
t_{PHL} , t_{PLH}	Maximum Output Propagation Delay	$C_L = 45\text{ pF}$	12	18	ns
t_{PZL} , t_{PZH}	Maximum Output Enable Time	$C_L = 45\text{ pF}$, $R_L = 1\text{ k}\Omega$	14	28	ns
t_{PLZ} , t_{PHZ}	Maximum Output Disable Time	$C_L = 5\text{ pF}$, $R_L = 1\text{ k}\Omega$	13	25	ns

AC ELECTRICAL CHARACTERISTICS

(MM74HCT540: $V_{CC} = 5.0\text{ V} \pm 10\%$, $t_r = t_f = 6\text{ ns}$, unless otherwise specified)

Symbol	Parameter	Conditions	T _A = 25°C		T _A = -40°C to 85°C	T _A = -55°C to 125°C	Unit
			Typ	Guaranteed Limits			
t _{PHL} , t _{PLH}	Maximum Output Propagation Delay	C _L = 50 pF	12	20	25	30	ns
		C _L = 150 pF	22	30	38	45	
t _{PZH} , t _{PZL}	Maximum Output Enable Time	R _L = 1 kΩ, C _L = 50 pF	15	30	38	45	ns
		R _L = 1 kΩ, C _L = 150 pF	20	40	50	60	ns
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	R _L = 1 kΩ, C _L = 50 pF	15	30	38	45	ns
t _{THL} , t _{TLH}	Maximum Output Rise and Fall Time	C _L = 50 pF	6	12	15	18	ns
C _{IN}	Maximum Input Capacitance		5	10	10	10	pF
C _{OUT}	Maximum Output Capacitance		15	20	20	20	pF
C _{PD}	Power Dissipation Capacitance (Note 3)	(per output) G̅ = V _{CC}	12	–	–	–	pF
		G̅ = GND	50	–	–	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

MM74HCT540, MM74HCT541

AC ELECTRICAL CHARACTERISTICS

(MM74HCT541: $V_{CC} = 5.0\text{ V}$, $t_r = t_f = 6\text{ ns}$, $T_A = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Unit
t_{PHL} , t_{PLH}	Maximum Output Propagation Delay	$C_L = 45\text{ pF}$	13	20	ns
t_{PZL} , t_{PZH}	Maximum Output Enable Time	$C_L = 45\text{ pF}$, $R_L = 1\text{ k}\Omega$	17	28	ns
t_{PLZ} , t_{PHZ}	Maximum Output Disable Time	$C_L = 5\text{ pF}$, $R_L = 1\text{ k}\Omega$	15	25	ns

AC ELECTRICAL CHARACTERISTICS

(MM74HCT541: $V_{CC} = 5.0\text{ V} \pm 10\%$, $t_r = t_f = 6\text{ ns}$, unless otherwise specified)

Symbol	Parameter	Conditions	T _A = 25°C		T _A = -40°C to 85°C	T _A = -55°C to 125°C	Unit
			Typ	Guaranteed Limits			
t _{PHL} , t _{PLH}	Maximum Output Propagation Delay	C _L = 50 pF	14	23	29	34	ns
		C _L = 150 pF	17	33	42	49	
t _{PZH} , t _{PZL}	Maximum Output Enable Time	R _L = 1 kΩ, C _L = 50 pF	17	30	38	45	ns
		R _L = 1 kΩ, C _L = 150 pF	22	40	50	60	ns
t _{PHZ} , t _{PLZ}	Maximum Output Disable Time	R _L = 1 kΩ, C _L = 50 pF	17	30	38	45	ns
t _{THL} , t _{TLH}	Maximum Output Rise and Fall Time	C _L = 50 pF	6	12	15	18	ns
C _{IN}	Maximum Input Capacitance		5	10	10	10	pF
C _{OUT}	Maximum Output Capacitance		15	20	20	20	pF
C _{PD}	Power Dissipation Capacitance (Note 4)	(per output) G̅ = V _{CC}	12	–	–	–	pF
		G̅ = GND	45	–	–	–	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

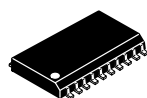
MM74HCT540, MM74HCT541

ORDERING INFORMATION

Device	Package	Shipping [†]
MM74HCT540MTCX	TSSOP-20 (Pb-Free)	2500 Units / Tape & Reel
MM74HCT541WM	SOIC-20 (Pb-Free)	38 Units / Tube
MM74HCT541MTCX	TSSOP-20 (Pb-Free)	2500 Units / Tape & Reel
MM74HCT541MTC	TSSOP-20 (Pb-Free)	75 Units / Tube
MM74HCT541WMX	SOIC-20 (Pb-Free)	1000 Units / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

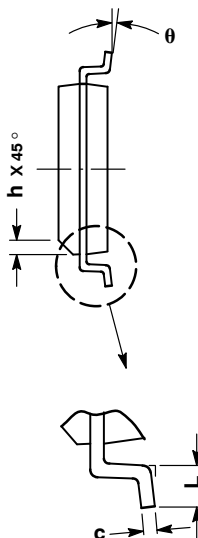
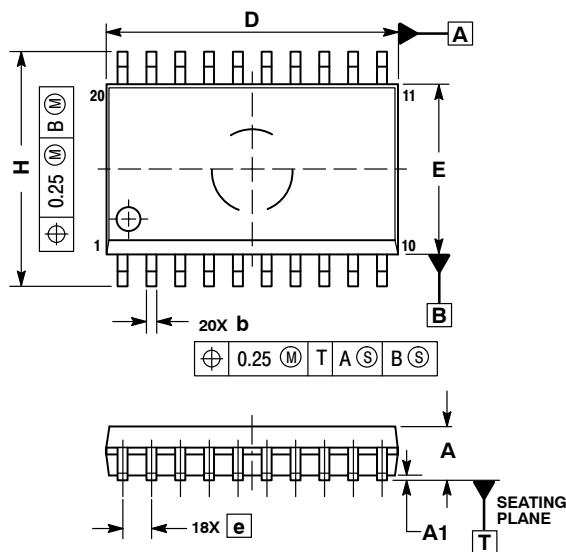
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-20 WB
CASE 751D-05
ISSUE H

DATE 22 APR 2015

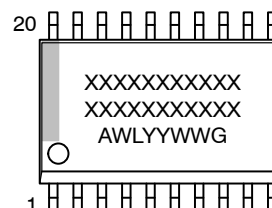


NOTES:

1. DIMENSIONS ARE IN MILLIMETERS.
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

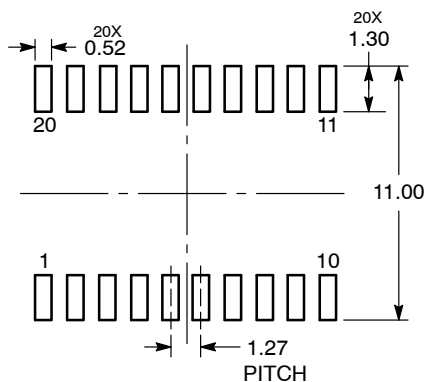
DIM	MILLIMETERS	
	MIN	MAX
A	2.35	2.65
A1	0.10	0.25
b	0.35	0.49
c	0.23	0.32
D	12.65	12.95
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.25	0.75
L	0.50	0.90
θ	0°	7°

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
G = Pb-Free Package

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

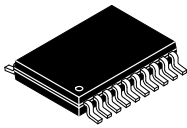
DOCUMENT NUMBER:	98ASB42343B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SOIC-20 WB	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

ON Semiconductor®

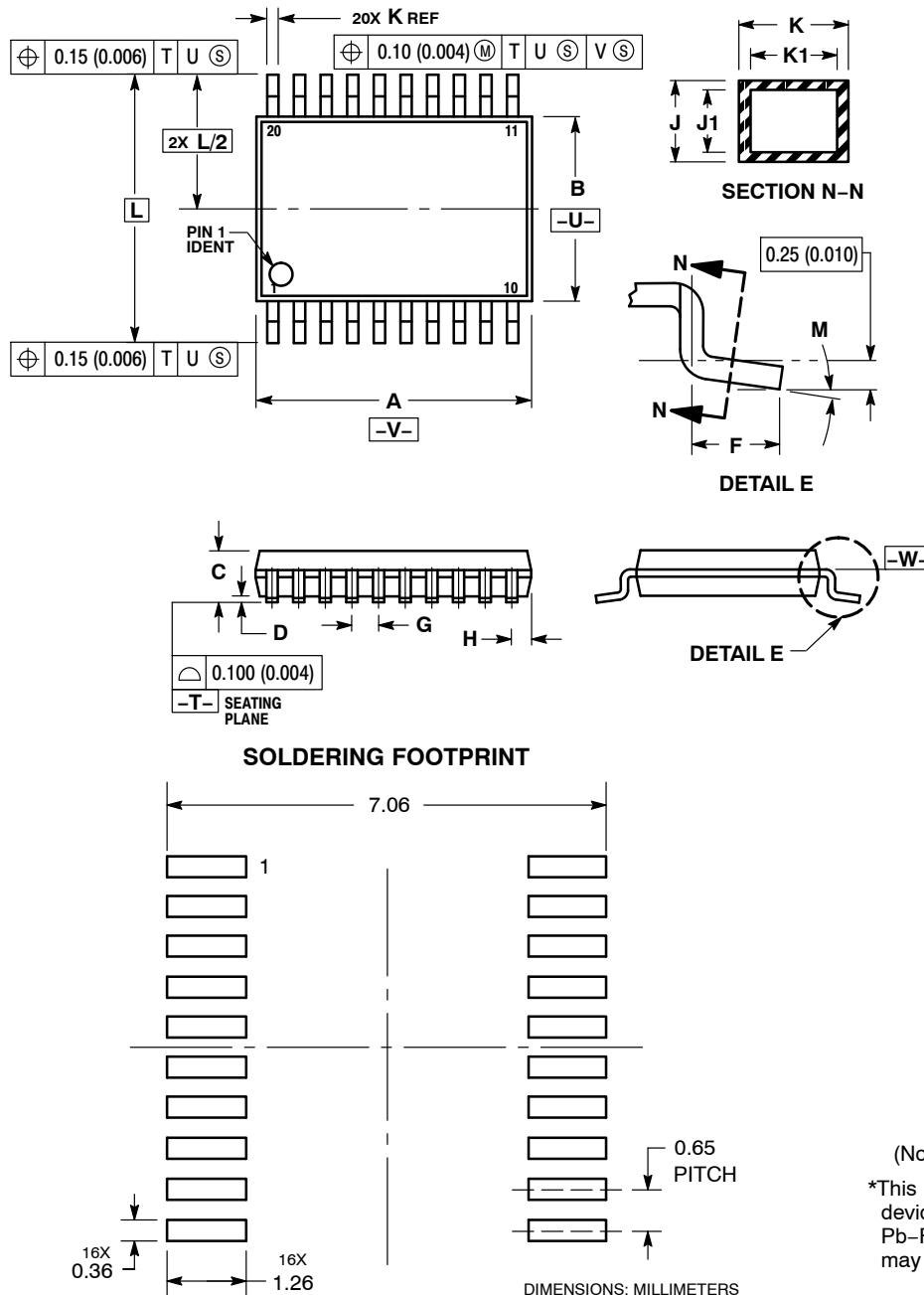
ON



SCALE 2:1

TSSOP-20 WB
CASE 948E
ISSUE D

DATE 17 FEB 2016

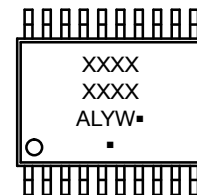


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

GENERIC MARKING DIAGRAM*



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

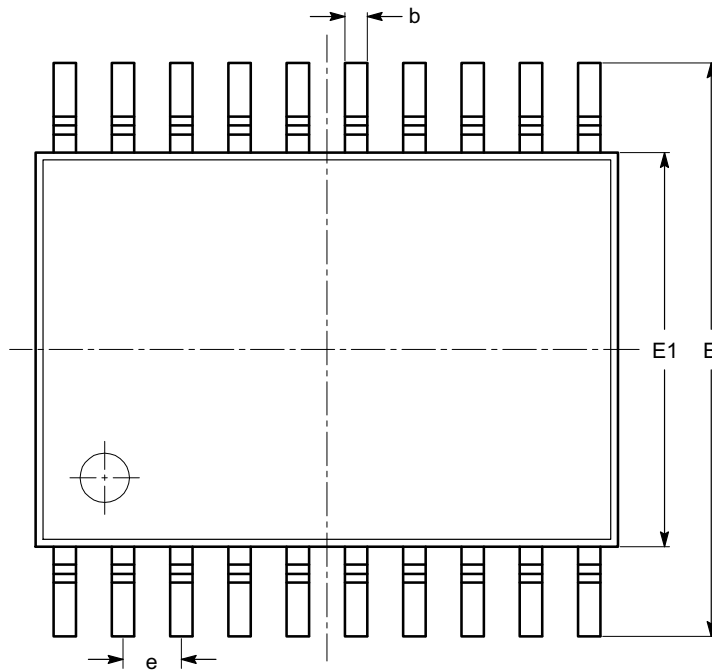
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

DOCUMENT NUMBER:	98ASH70169A	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TSSOP-20 WB	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

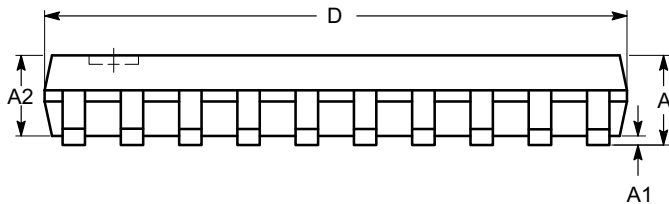
TSSOP20, 4.4x6.5
CASE 948AQ-01
ISSUE A

DATE 19 MAR 2009

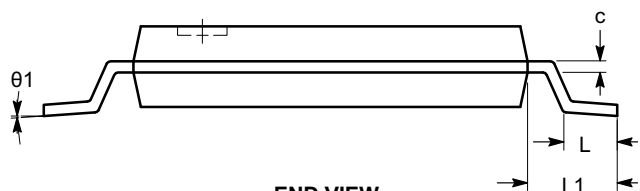


TOP VIEW

SYMBOL	MIN	NOM	MAX
A			1.20
A1	0.05		0.15
A2	0.80		1.05
b	0.19		0.30
c	0.09		0.20
D	6.40	6.50	6.60
E	6.30	6.40	6.50
E1	4.30	4.40	4.50
e	0.65 BSC		
L	0.45	0.60	0.75
L1	1.00 REF		
θ	0°		8°



SIDE VIEW



END VIEW

Notes:

- (1) All dimensions are in millimeters. Angles in degrees.
- (2) Complies with JEDEC MO-153.

DOCUMENT NUMBER:	98AON34453E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	TSSOP20, 4.4X6.5	PAGE 1 OF 1

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT

North American Technical Support:

Voice Mail: 1 800-282-9855 Toll Free USA/Canada

Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative